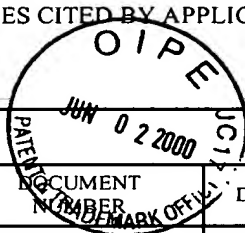


Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 0057-2534-2YY DIV		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT (Use Several Sheets if Necessary)				APPLICANT Shuichi UENO, et al.			
				FILING DATE HEREWITH		GROUP 2823	
				JC675 U.S. PTO 09/429283 10/28/99			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	AA	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
G	AL	4-157766	5/29/92	JAPAN			XX
G	AM	7-176743	7/14/95	JAPAN			XX
	AN						
	AO						
	AP						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
G	AR	C. KUO, "EMBEDDED FLASH MEMORY APPLICATIONS, TECHNOLOGY AND DESIGN", 1995 IEDM SHORT COURSE, Motorola Inc., Austin, Texas, 1995.					
	AS						
	AT						
EXAMINER					DATE CONSIDERED		
FOURSON					6/17/00		
*EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 0057-2534-2YY		SERIAL NO. 09/429,283	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Shuichi UENO, et al.			
				FILING DATE October 28, 1999		GROUP 2811 2823	



U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
G F F	AA	5,514,902	05/07/96	Y. KAWASAKI, et al.	—	—	
	AB	5,567,638	10/22/96	Y.-H. LIN, et al.	—	—	
	AC	5,607,868	03/04/97	N. CHIDA, et al.			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
				YES	NO	
G F	AO	4-157766	05/29/92	JAPAN (with English Abstract)	—	X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)		
G	AW	T. KUROI, et al., Japanese Journal of Applied Physics, Vol. 34, No. 2B, pps. 771-775, "THE IMPACT OF NITROGEN IMPLANTATION INTO HIGHLY DOPED POLYSILICON GATES OF HIGHLY RELIABLE AND HIGH-PERFORMANCE SUB-QUARTER-MICRON DUAL-GATE COMPLEMENTARY METAL OXIDE SEMICONDUCTOR," February 1, 1995
G	AX	A.I. CHOU et al., 1997 IEEE INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUM PROCEEDINGS, Vol. SYMP. 35, pps. 174-177, "THE EFFECTS OF NITROGEN IMPLANT INTO GATE ELECTRODE ON THE CHARACTERISTICS OF DUAL-GATE MOSFETS WITH ULTRA-THIN OXIDE AND OXYNITRIDES," 1997
	AY	
	AZ	

Examiner <i>Fourson</i>	Date Considered <i>6/17/00</i>
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.